INFORMATION DISCLOSURE CITATION IN AN				ATTY. DOCKET NO. <b>57810-033</b>		SERIAL NO.		
APPLICATION						:	e F	
		APPLICANT Nobuhiko HAYASHI			08405			
(PTO-1449)				FILING DATE February 28, 2002		GROUP	410AK	10/
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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME		CLASS	SUBCLASS	FII	LING DATE
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INTIALS					CLASS		Yes	No
I for	2000-164989	6/16/2000	Japan (w/ English Abstract)		<u> </u>			
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.